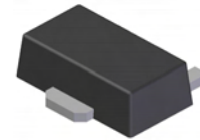


**Features**

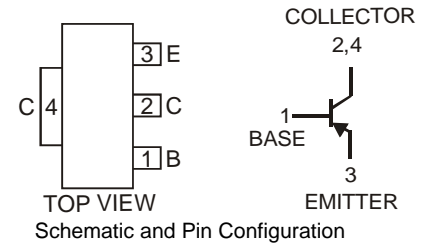
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DCX56)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L

**Mechanical Data**

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Peak Pulse Current	I <sub>CM</sub>	-1.5	A
Continuous Collector Current	I <sub>C</sub>	-1	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient Air @ T <sub>A</sub> = 25°C (Note 3)	R <sub>θJA</sub>	125	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions	
<b>OFF CHARACTERISTICS (Note 4)</b>							
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-100	—	—	V	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-80	—	—	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5	—	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0	
Collector Cutoff Current	I <sub>CBO</sub>	—	—	-100 -20	nA μA	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0 V <sub>CB</sub> = -30V, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C	
Emitter Cutoff Current	I <sub>EBO</sub>	—	—	-100	nA	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0	
<b>ON CHARACTERISTICS (Note 4)</b>							
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	—	-0.5	V	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA	
Base-Emitter Turn-On Voltage	V <sub>BE(SAT)</sub>	—	—	-1.0	V	I <sub>C</sub> = -500mA, V <sub>CE</sub> = -2V	
DC Current Gain	h <sub>FE</sub>	DCX53, DCX53-16	63	—	—	—	I <sub>C</sub> = -5mA, V <sub>CE</sub> = -2V
			40	—	—	—	I <sub>C</sub> = -500mA, V <sub>CE</sub> = -2V
		DCX53	63	—	250	—	I <sub>C</sub> = -150mA, V <sub>CE</sub> = -2V
			100	—	250	—	I <sub>C</sub> = -150mA, V <sub>CE</sub> = -2V
<b>SMALL SIGNAL CHARACTERISTICS</b>							
Current Gain-Bandwidth Product	f <sub>T</sub>	—	200	—	MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5V, f = 100MHz	
Output Capacitance	C <sub>obo</sub>	—	—	25	pF	V <sub>CB</sub> = -10V, f = 1MHz	

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

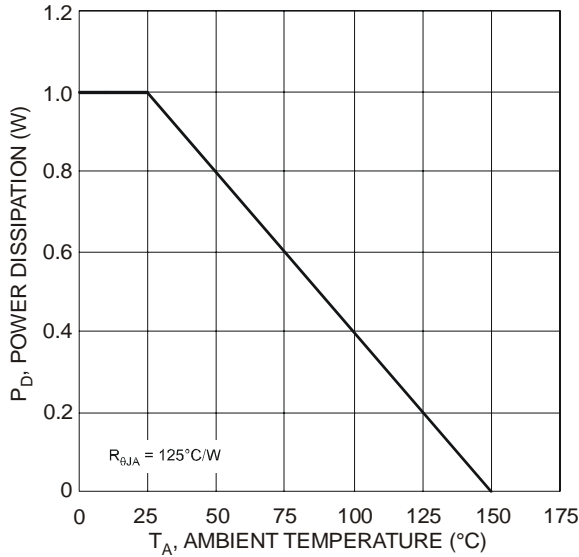


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

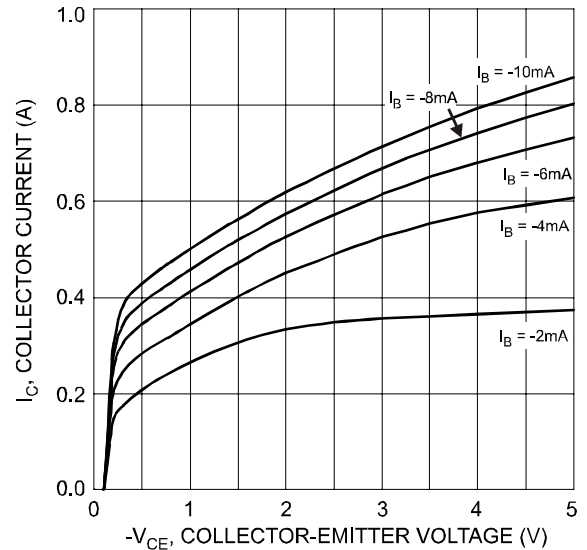


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

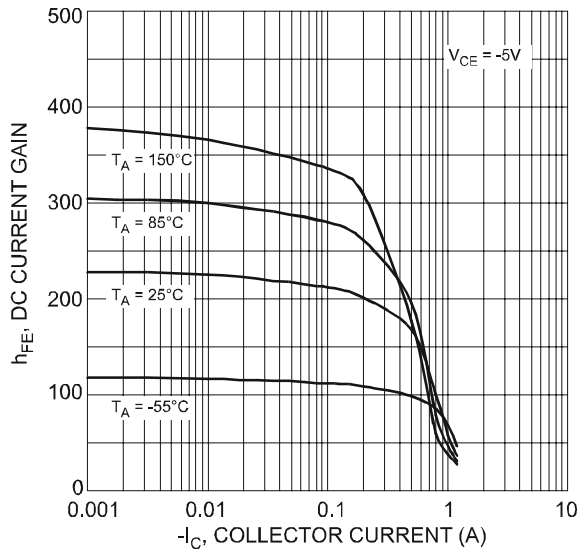


Fig. 3 Typical DC Current Gain vs. Collector Current

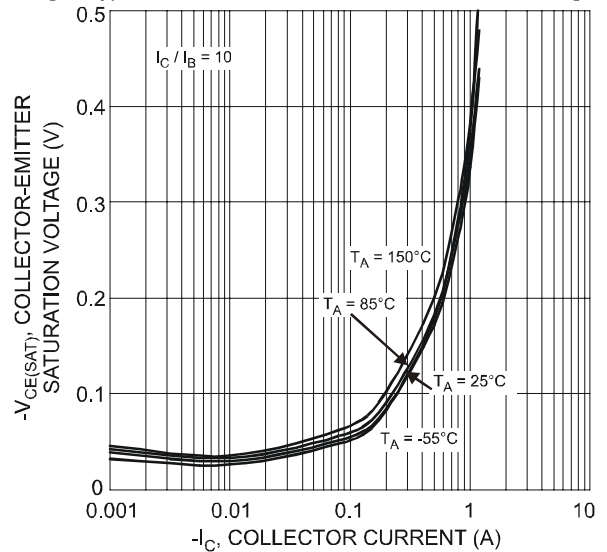


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

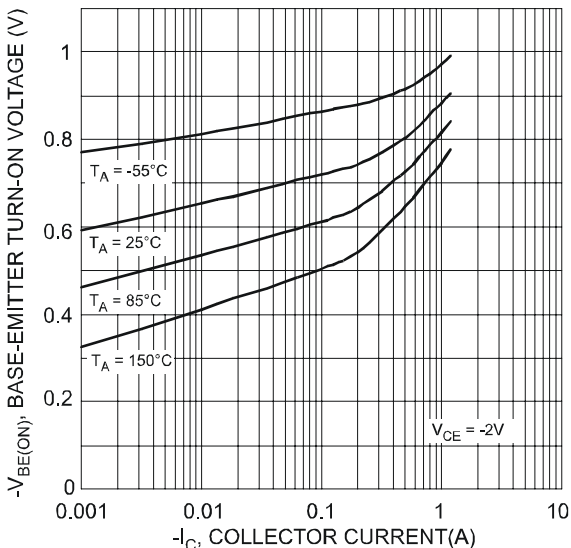


Fig. 5. Typical Base-Emitter Turn-On Voltage vs. Collector Current

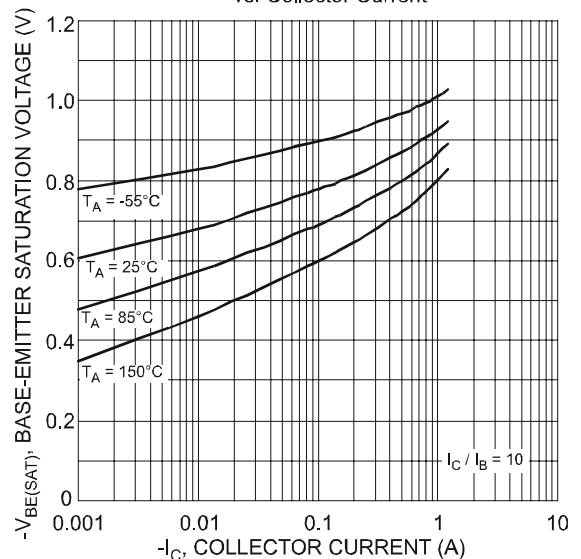
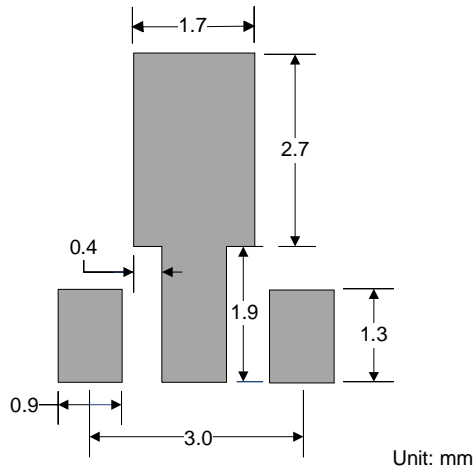


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



## Suggested Pad Layout



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